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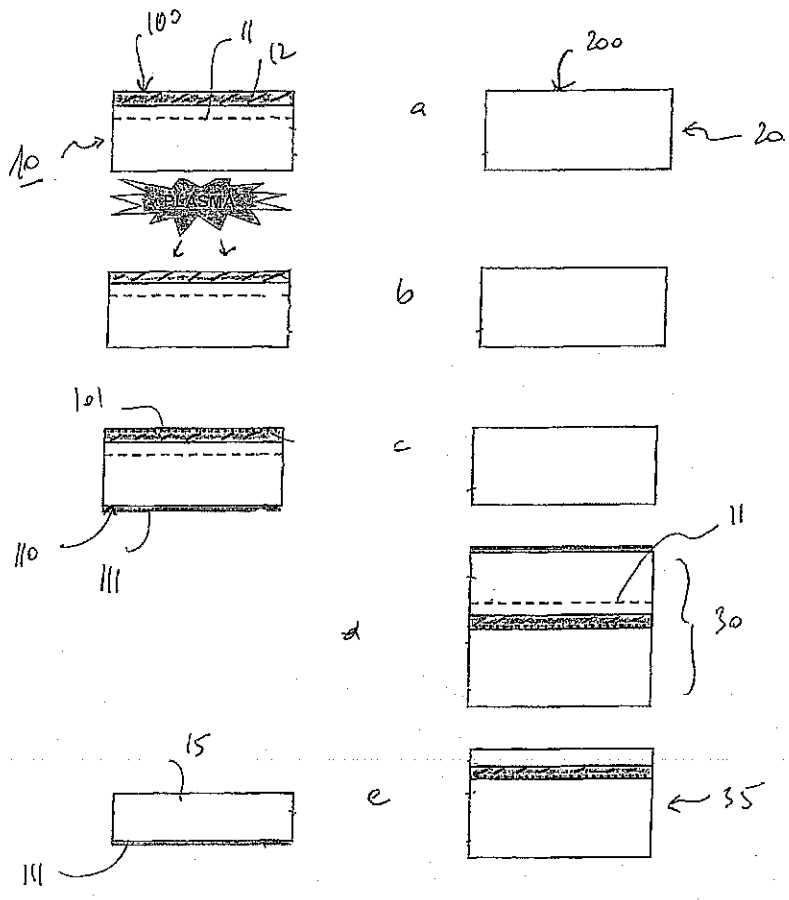
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(54) Title: TRANSFER METHOD WITH A TREATMENT OF A SURFACE TO BE BONDED



(57) Abstract: The invention concerns a method for transferring from a top donor wafer (10) a layer of material onto a receiving handle wafer (20), the top and receiving wafers comprising respective surfaces to be bonded, the method comprising: • a treatment step for treating at least a surface to be bonded, the treatment of a given surface of a wafer generating on the opposed surface of said wafer a contamination, • a bonding step for direct bonding the surfaces to be bonded of the top and handle wafers, in order to form an intermediate multilayer wafer (30), • a removal step for removing excess material from the top wafer, the method being characterized in that during the treatment step only the surface to be bonded of the top wafer is treated.

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